

AMENDMENT TO THE CLAIMS

1-18 (Canceled).

19. (Currently Amended) An array substrate for an active matrix type liquid crystal display (LCD) device, comprising:

a substrate;

a gate line on said substrate, wherein said gate line includes a gate pad;

a first insulating layer on said gate line and said substrate;

a semiconductor layer on said first insulating layer and over a portion of said gate line;

a data line over said first insulating layer and that crosses said gate line, said data line including a protruding portion that projects in a direction of said semiconductor layer and that forms a source electrode, wherein an end portion of the semiconductor layer under the data line is substantially a same width as an end portion of the data line, wherein said data line further includes a data pad;

a drain electrode spaced apart from said source electrode and extending into a rectangular region partially defined by said gate and data lines;

a passivation layer on said drain electrode, said passivation layer having a drain contact hole that exposes said drain electrode; and

a pixel electrode formed over the passivation layer, said pixel electrode electrically connecting to said drain electrode via said drain contact hole, wherein said pixel electrode extends over a portion of said gate line so as to form a storage capacitor comprised of ~~said pixel electrode a capacitor electrode extending from the pixel electrode~~, said gate line, and said first insulating layer therebetween, wherein said storage capacitor further includes a short-preventing part disposed between said pixel electrode and said gate line.

wherein the short-preventing part has a stepped portion that overlaps a stepped end portion of the gate line.

20. (Original) The array substrate of claim 19, wherein said short-preventing part includes said semiconductor layer and said passivation layer.

21. (Original) The array substrate of claim 20, wherein said short-preventing part further includes an ohmic contact layer, and a conducting material between said semiconductor layer and said passivation layer.